

**IN THE CLAIMS:**

Please cancel claims 6, 13, and 19; add new claims 24, 25, and 26; and, amend the remaining claims follows:

1. (Currently Amended) A method of forming a phase shift mask, said method comprising:  
  
forming an opaque layer on a transparent substrate;  
  
performing a first patterning of said opaque layer to expose a first region of said transparent substrate, wherein said first region comprises an uninterrupted rectangular surface;  
  
etching said first region of said transparent substrate to create a phase shift region within said transparent substrate; and  
  
performing additional patterning of said opaque layer to expose a second region of said transparent substrate, such that said second region comprises a similar shape and size as said first region, wherein said second region is adjacent said first region, and wherein said additional patterning process enlarges an opening formed in said first patterning process.
2. (Cancelled).
3. (Original) The method in claim 1, wherein said first region and said second region comprise a continuous area of said transparent substrate.

4. (Original) The method in claim 1, wherein said opaque layer comprises a chrome mask.

5. (Original) The method in claim 1, wherein said transparent substrate comprises a quartz substrate.

6. (Cancelled).

7. (Cancelled).

8. (Currently Amended) A method of forming a phase shift mask, said method comprising:

forming an opaque layer on a transparent substrate;

performing a first patterning of said opaque layer to expose first regions of said transparent substrate, wherein said first regions comprise uninterrupted rectangular surfaces;

etching said first regions of said transparent substrate to create phase shift regions within said transparent substrate; and

performing additional patterning of said opaque layer to expose second regions and third regions of said transparent substrate, such that said second regions comprise similar shapes and sizes as said first regions, wherein said second regions are adjacent said first regions and said third regions are separated from said first regions, such that said third

regions are devoid of phase shift features, and wherein said additional patterning process enlarges openings formed in said first patterning process.

9. (Cancelled).

10. (Original) The method in claim 8, wherein each pair of said first regions and said second regions comprises a continuous area of said transparent substrate.

11. (Original) The method in claim 8, wherein said opaque layer comprises a chrome mask.

12. (Original) The method in claim 8, wherein said transparent substrate comprises a quartz substrate.

13. (Cancelled).

14. (Cancelled).

15. (Currently Amended) A method of forming a phase shift mask, said method comprising:

forming an opaque chrome layer on a transparent quartz substrate;

performing a first patterning of said opaque chrome layer to expose a first region of said transparent quartz substrate, wherein said first region comprises an uninterrupted rectangular surface;

etching said first region of said transparent quartz substrate to create a phase shift region within said transparent quartz substrate; and

performing additional patterning of said opaque chrome layer to expose a second region of said transparent quartz substrate, such that said second region comprises a similar shape and size as said first region, wherein said second region is adjacent said first region, and wherein said additional patterning process enlarges an opening formed in said first patterning process.

16. (Cancelled).

17. (Original) The method in claim 15, wherein said first region and said second region comprise a continuous area of said transparent quartz substrate.

18. (Original) The method in claim 15, wherein said opaque chrome layer comprises a chrome mask.

19. (Cancelled).

20. (Cancelled).

21. (Previously Presented) The method in claim 1, wherein said etching and said additional patterning both attack said substrate.
22. (Previously Presented) The method in claim 8, wherein said etching and said additional patterning both attack said substrate.
23. (Previously Presented) The method in claim 15, wherein said etching and said additional patterning both attack said substrate.
24. (New) The method in claim 1, wherein said uninterrupted rectangular surface lacks an intervening structure.
25. (New) The method in claim 8, wherein said uninterrupted rectangular surfaces lack intervening structures.
26. (New) The method in claim 15, wherein said uninterrupted rectangular surface lacks an intervening structure.